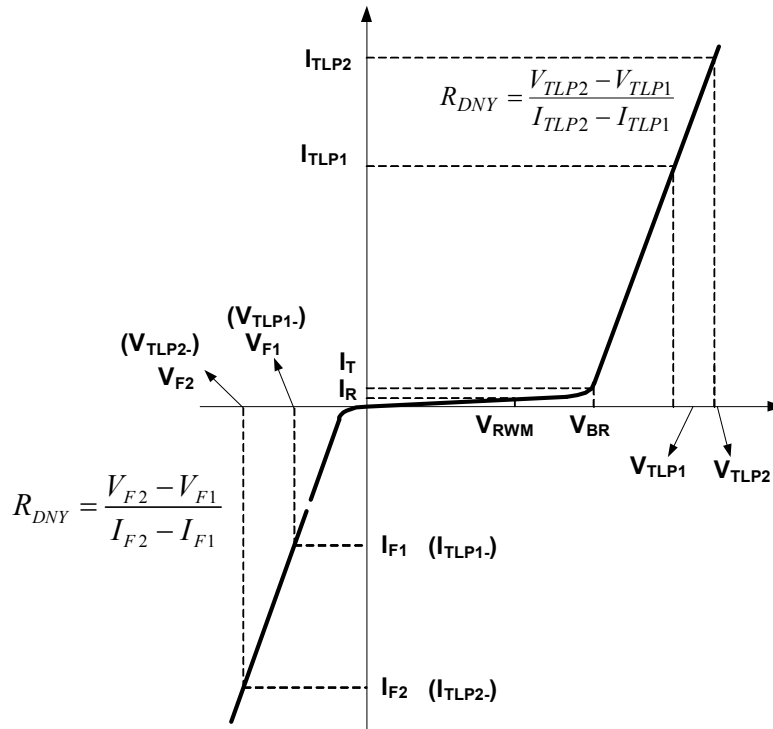






## Electrical Characteristics

T<sub>A</sub> = 25°C unless otherwise specified. Any I/O Pin to GND.



Pin1 & Pin 10 (D+, D- of USB 2.0)						
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
$V_{RWM}$	Reverse Working Voltage				5.5	V
$V_{BR}$	Reverse Breakdown Voltage	$I_T = 100\mu A$	6.6			V
$I_R$	Reverse Leakage Current	$V_T = \text{Max}, V_{RWM}$			1	$\mu A$
$V_F$	Forward Voltage		0.7	0.85	0.95	V
$V_{CL}$	Clamping Voltage <sup>(3)(4)</sup> (100ns Transmission Line Pulse)	$I_{TLP} = 1A$ $I_{TLP} = -1A$		11 -1.5		V
		$I_{TLP} = 16A$ $I_{TLP} = -16A$		18 -7.5		
$R_{DNY}$	Dynamic Resistance <sup>(3)(4)</sup>	$I_{TLP} = 1A$ to $16A$ $I_{TLP} = -1A$ to $-16A$			0.45 0.40	
$I_{PP}$	Peak Pulse Current <sup>(3)</sup> IEC61000-4-5 Surge 8/20 $\mu s$	Any I/O Pin to GND GND to any I/O Pin			$\pm 4$	A
$V_{CL}$	Clamping Voltage <sup>(3)</sup> IEC61000-4-5 Surge 8/20 $\mu s$	$I_{PP} = 1A$ $I_{PP} = -1A$		10 -2		V
		$I_{PP} = 4A$ $I_{PP} = -4A$		12.5 -4.5		
$C_j$	Junction Capacitance <sup>(3)</sup>	$V_{BUS} = 3.3V, f = 1MHz,$ Any I/O Pin to GND		1.75	2	pF

### Notes:

3. These specifications are guaranteed by design and characterization.
4. Measurements performed using a 100ns Transmission Line Pulse (TLP) system.













